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MODIFIED PTO/SB/08 A & B (06-03)

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Substitute for Form 1449 A & B/PTO				•	Application Number	Not Yet Assigned	
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STATEMENT BY APPLICANT					Filing Date	November 29, 2005	
					First Named Inventor	Munehiro TADA	
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	Sheet	1	of	1	Attorney Docket Number	Q91732	

U.S. PATENT DOCUMENTS						
	Cite No. ¹	Document Nu	ımber			
Examiner Initials*		Number	Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
		US 2003/0001282	A1	01-02-2003	Herman Meynen	
		US				
		US				
		US				
		US				
		US				
		US				
		US				
		US				

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document			Publication Date	Name of Patentee or	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)		Applicant of Cited Document	Translation
		JР	2000-183166	Α	06-30-2000	NEC CORP.	
		wo	2001/054190	A1	07-26-2001	ADVANCED MICRO DEVICES	
		WO	2002/058134	Al	07-25-2002	STMICROELECTRONICS S.A.	
1		JР	2002-83870	Α	03-22-2002	TOKYO ELECTRON LTD.	
		JР	2002-9078	Α	01-11-2002	ASM MICROCHEMISTRY OY	
	***	JР	2000-294634	Α	10-20-2000	NEC CORP.	
		JР	2004-200203	Α	07-15-2004	SEMICONDUCTOR LEADING, et al.	
		JР	2004-193326	Α	07-08-2004	SONY CORP.	
		JP	2003-347403	Α	12-05-2003	FUJITSU LTD.	
						<u> </u>	<u> </u>

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶	
		Tada, M., et al. "BARRIER-METAL-FREE (BMF), Cu DUAL-DAMASCENE INTERCONNECTS WITH Cu-epi-CONTACTS BURIED IN ANTI-DIFFUSIVE, LOW-k ORGANIC FILM," 2001 Symposium on VLSI Technology, June 12, 2001, pages 13-14.		
		Tada, M., et al. "A 65nm-NODE Cu INTERCONNECT TECHNOLOGY USING POROUS SIOCH FILM (K=2.5) COVERED WITH ULTRA-THIN, LOW-k PORE SEAL (k=2.7), International Electron Devices Meeting 2003 Technical Digest, December 8-10, 2003, pages 35.2.1 to 35.2.4.		
				

Examiner Signature	Date Considered	1

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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